# <u>onsemi</u>

### 15 A, 600 V, STEALTH™ II Diode

## FFPF15S60S

#### Description

The FFPF15S60S is STEALTH<sup>™</sup> II rectifier with soft recovery characteristics. It is silicon nitride passivated ion–implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

#### Features

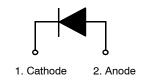
- Stealth Recovery  $T_{rr}$ = 35 ns (@  $I_F$ = 15 A)
- Max Forward Voltage,  $V_F$ = 2.6 V (@ T<sub>C</sub>= 25°C)
- 600 V Reverse Voltage and High Reliability
- Improved dv/dt Capability
- This Device is Pb-Free and is RoHS Compliant

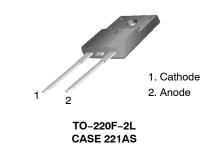
#### Applications

- General Purpose
- Switching Mode Power Supply
- Boost Diode in Continuous Mode Power Factor Corrections
- Power Switching Circuits

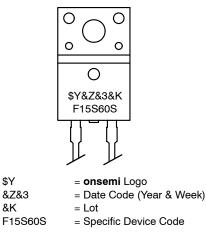
Symbol	Parameter	Value	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	600	V	
V <sub>RWM</sub>	/ <sub>RWM</sub> Working Peak Reverse Voltage		V	
V <sub>R</sub>	R DC Blocking Voltage		V	
I <sub>F(AV)</sub>	(AV) Average Rectified Forward Current @ $T_C = 52^{\circ}C$		А	
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 60 Hz Single Half-Sine Wave	150	A	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	– 65 to +175	°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.









#### ORDERING INFORMATION

Device		Package	Shipping
I	FFPF15S60STU	TO-220F-2L	50 / Tube

### FFPF15S60S

#### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Maximum Thermal Resistance, Junction to Case	4.6	°C/W

#### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter		Min.	Тур.	Max	Unit
V <sub>FM</sub> (Note 1)	I <sub>F</sub> = 15 A I <sub>F</sub> = 15 A	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C		2.1 1.6	2.6 _	V
I <sub>RM</sub> (Note 1)	V <sub>R</sub> = 600 V V <sub>R</sub> = 600 V	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C	-	-	100 500	μΑ
t <sub>rr</sub>	$I_F$ =1 A, di <sub>F</sub> /dt = 100 A/µs, V <sub>R</sub> = 30 V	$T_{C} = 25^{\circ}C$	-	21	30	ns
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	I <sub>F</sub> = 15 A, di <sub>F</sub> /dt = 200 A/μs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 25°C		23 2.5 0.7 29	35 - - -	ns A nC
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	I <sub>F</sub> = 15 A, di <sub>F</sub> /dt = 200 A/μs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 125°C		55 4.3 1.1 118	- - -	ns A nC
W <sub>AVL</sub>	Avalanche Energy (L = 40 mH)	•	20	-	-	mJ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse: Test Pulse width = 300  $\mu$ s, Duty Cycle = 2%

#### **TEST CIRCUIT AND WAVEFORMS**

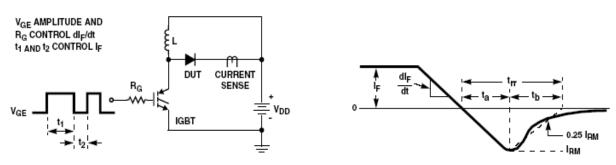
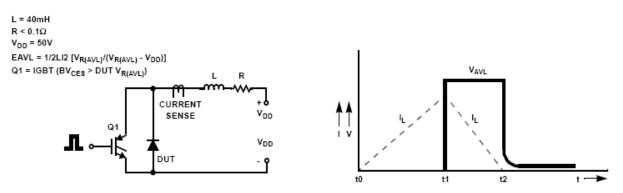


Figure 1. Diode Reverse Recovery Test Circuit & Waveform





#### FFPF15S60S

#### **TYPICAL PERFORMANCE CHARACTERISTICS**

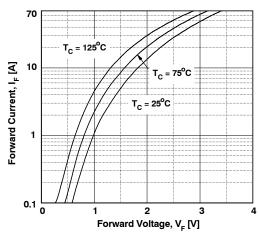


Figure 3. Typical Forward Voltage Drop vs. Forward Current

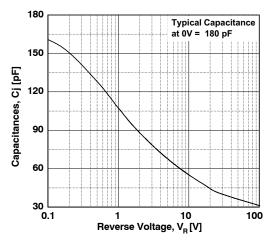


Figure 5. Typical Junction Capacitance

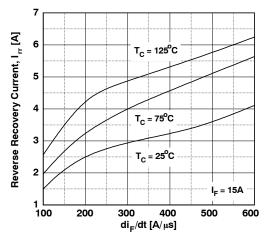


Figure 7. Typical Reverse Recovery Current vs. di/dt

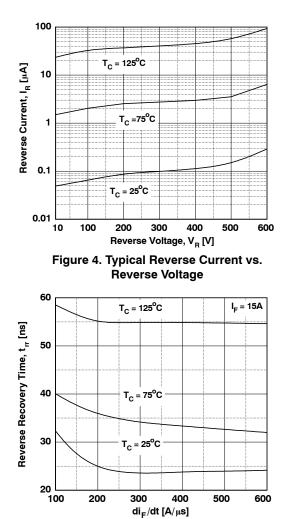


Figure 6. Typical Reverse Recovery Time vs. di/dt

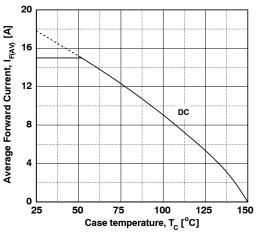
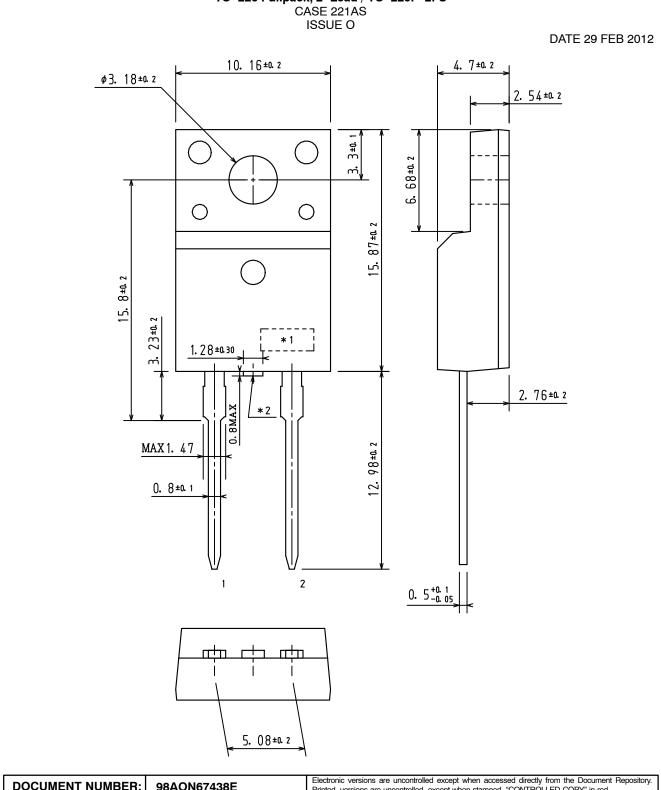


Figure 8. Forward Current Derating Curve

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TO-220 Fullpack, 2-Lead / TO-220F-2FS

DATE 29 FEB 2012

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